

EO-532-H/100~500μJ

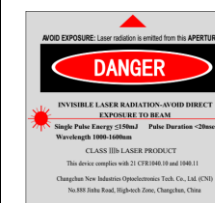
HIGH ENERGY DIODE PUMPED ALL-SOLID-STATE Q-SWITCHED LASER

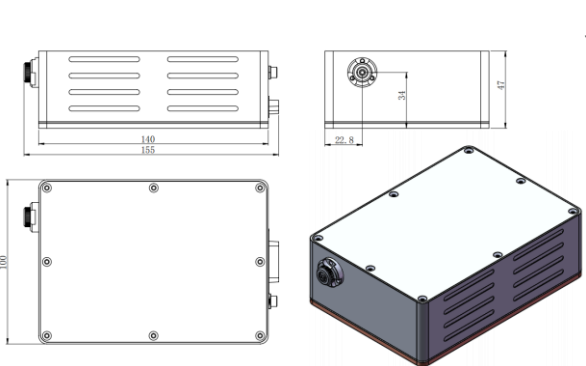
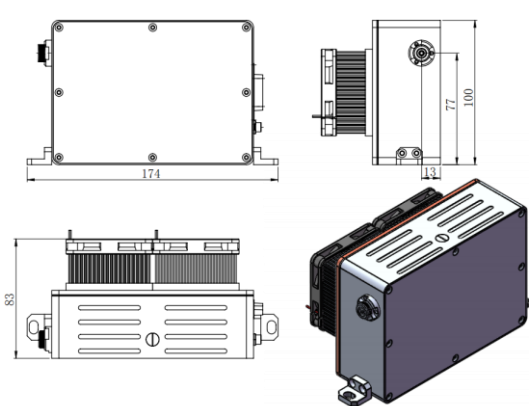
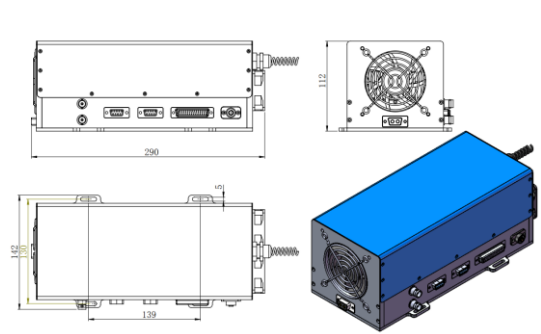
High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in radar, topography measurement, ranging, scientific research, and so on.



SPECIFICATIONS

Wavelength (nm)	532±1	
Operating mode	Q-switched: EO (Electro-optic)	
Single pulse energy (μJ)	300	500
Pulse duration (ns)	<5	
Rep. rate (kHz)	One fixed value between 2~7kHz	
Energy stability (rms)	<1% , <2%	
M ²	<1.5	
Pointing stability (urad, std)	<20	
Beam divergence, full angle (mrad)	<3	
Beam diameter (mm)	~1	
Beam height from base plate (mm)	34	77
Warm-up time (minutes)	<15	
Cooled method	Conduction (EO-532-H- I)	Air cooled (EO-532-H- II)
Operating temperature (°C)	15~30	
Power supply (DC 15V, 20A)	PSU-EO-H	
Expected lifetime (hours)	10000	
Warranty period	1 year	
Options	Repetition rate 1~200KHz available. Volume will be increased appropriately.	



EO-532-H- I	EO-532-H- II	PSU-EO-H(DC 15V, 20A)
 <p>155(L)×100(W)×47 (H)mm³ Heat dissipation is offered by customer (>70W)</p>	 <p>174(L)×83(W)×100 (H)mm³</p>	 <p>290 (L) ×142(W) ×112(H) mm³</p>